

Patent Abstracts of Japan

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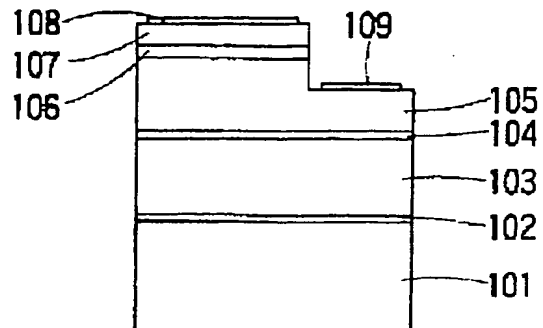
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TITLE : SEMICONDUCTOR LIGHT EMITTING
ELEMENT AND SEMICONDUCTOR
LIGHT EMITTING DEVICE



ABSTRACT : PROBLEM TO BE SOLVED: To provide a semiconductor light emitting element and semiconductor light emitting device which have a sufficient life and can select a light emitting wavelength in a wide wavelength range of visible lights such as blue and green lights.

SOLUTION: A semiconductor light emitting element superior in light emitting characteristics, element life, etc., is provided, comprising a first light emitting layer 106 which emits a light when a current is injected, and second light emitting layer 104 which absorbs a light from the first light emitting layer and outputs a converted wavelength. It is composed of a laminate structure of GaN semiconductors, etc., having e.g. a GaN as the first light emitting layer 106 and the second InGaN-based light emitting layer 104 which absorbs the light from this light emitting layer to emit a light as light excitation.

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